AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

1. (Currently amended): A polishing slurry for semiconductor planarization containing cerium oxide particles and water, wherein the content of the cerium oxide particles having a diameter of at least 3 μm is not more than 500, ppm ~~in a whole solid~~ calculated based on the weight of particles obtained by filtering with a film type filter for analysis on which hole diameters of 3 μm are formed and the weight of all the solids in the polishing slurry.

2. (Original): The polishing slurry for semiconductor planarization according to claim 1, further containing a dispersing agent.

3. (Currently amended): The polishing slurry for semiconductor planarization according to claim 1 or 2, wherein ~~the particle diameter is not more than 1 μm in~~ 99 % by volume of the ~~whole~~ cerium oxide particles have a size of less than 1 μm.

4. (New): The polishing slurry for semiconductor planarization according to claim1, wherein the median diameter (D50) of secondary particles of the cerium oxide particles is in the range of 0.03 to 0.5 μm.

5. (New): The polishing slurry for semiconductor planarization according to claim 1, wherein said polishing slurry is produced by filtering cerium oxide particles multiple times through a filter, wherein holes of the filter are formed by superposing filter fibers and by reducing diameters of the holes continuously from the outside of the filter to the inside, and wherein the filter fibers are not mutually fixed.

6. (New): A method for producing a polishing slurry for semiconductor planarization, comprising

grinding cerium oxide particles,

mixing at least a dispersing agent and water with the cerium oxide particles to prepare a single-liquid type polishing slurry or a double-liquid type polishing slurry,

filtering the polishing slurry through a filter wherein holes of the filter are formed by superposing filter fibers and reducing the diameter of the holes continuously from the outside of the filter to the inside, wherein the filter fibers are not mutually fixed, and

performing said filtering multiple times until the content of the cerium oxide particles having a diameter of at least 3 μm is not more than 500 ppm, calculated based on the weight of particles obtained by filtering with a film type filter for analysis on which hole diameters of 3 μm are formed and the weight of all the solids in the polishing slurry.

7. (New): The method for producing a polishing slurry for semiconductor planarization according to claim 6, wherein the filtering step includes a classification step.